

Complementary N- and P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ)
N-Channel	40	0.030 at V _{GS} = 10 V	8	9.6
		0.034 at V _{GS} = 4.5 V	8	
P-Channel	- 40	0.032 at V _{GS} = - 10 V	- 8	21
		0.041 at V _{GS} = - 4.5 V	- 8	

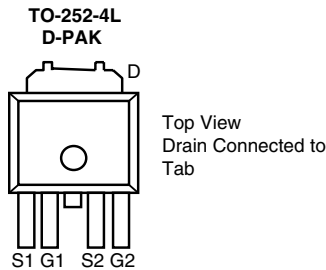
FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

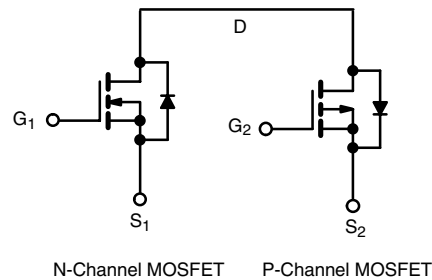


APPLICATIONS

- CCFL Inverter
- LCD TV and Monitor



Ordering Information: SUD50NP04-62-T4-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V _{DS}	40	- 40	V	
Gate-Source Voltage	V _{GS}	± 16			
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	8	- 8	A
		T _C = 70 °C	8	- 8	
		T _A = 25 °C	8 ^{b, c}	- 8 ^{b, c}	
		T _A = 70 °C	8 ^{b, c}	- 8 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	35	- 35	A	
Source-Drain Current Diode Current	I _S	T _C = 25 °C	8		- 8
		T _A = 25 °C	5 ^{b, c}		- 5.5 ^{b, c}
Pulsed Source-Drain Current	I _{SM}	35	- 35	mJ	
Single Pulse Avalanche Current	I _{AS}	10	20		
Single Pulse Avalanche Energy	E _{AS}	5	20	W	
Maximum Power Dissipation	P _D	T _C = 25 °C	15.6		23.5
		T _C = 70 °C	10		15
		T _A = 25 °C	6 ^{b, c}		6.7 ^{b, c}
		T _A = 70 °C	3.9 ^{b, c}	4.3 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	N-Channel		P-Channel		Unit
		Typ	Max	Typ	Max	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	17	20.5	15.2	18.5	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	6.6	8	4.4	5.3	

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 Board.
- t = 10 sec.
- Maximum under Steady State conditions is 53 °C/W (N-Channel) and 50 °C/W (P-Channel).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	40			V
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-40			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		37		
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		-38		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	N-Ch		-5		
		$I_D = -250\text{ }\mu\text{A}$	P-Ch		4.0		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.6		2.0	
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.8		-2.2	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	N-Ch			100	nA
			P-Ch			-100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			10	
		$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-10	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	20			A
		$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-20			
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$	N-Ch		0.025	0.030	Ω
		$V_{GS} = -10\text{ V}, I_D = -6\text{ A}$	P-Ch		0.026	0.032	
		$V_{GS} = 4.5\text{ V}, I_D = 4.8\text{ A}$	N-Ch		0.028	0.034	
		$V_{GS} = -4.5\text{ V}, I_D = -4.9\text{ A}$	P-Ch		0.034	0.041	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6\text{ A}$	N-Ch		20		S
		$V_{DS} = -15\text{ V}, I_D = -6\text{ A}$	P-Ch		17		
Dynamic^a							
Input Capacitance	C_{iss}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ $V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		855		μF
			P-Ch		1505		
Output Capacitance	C_{oss}		N-Ch		105		
			P-Ch		230		
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		65		μF
			P-Ch		175		
Total Gate Charge	Q_g	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	N-Ch		21	32	nC
		$V_{DS} = -20\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	P-Ch		41	62	
Gate-Source Charge	Q_{gs}	$V_{DS} = 20\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	N-Ch		9.6	14.5	
			P-Ch		21	31	
Gate-Drain Charge	Q_{gd}	$V_{DS} = -20\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$	N-Ch		2.3		
			P-Ch		4.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$	N-Ch		2.5	3.8	Ω
			P-Ch		6.5	10	



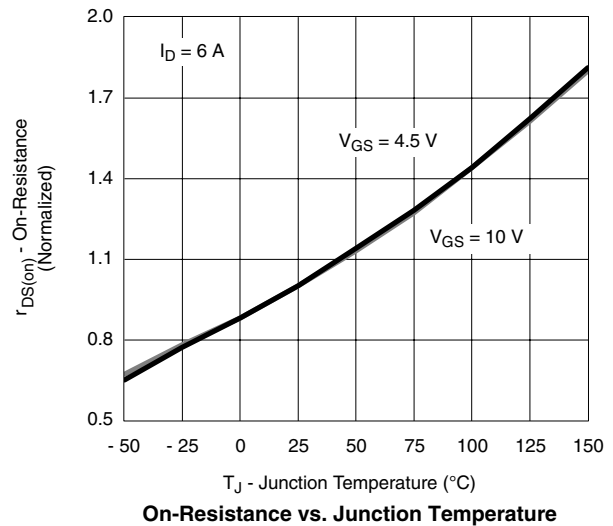
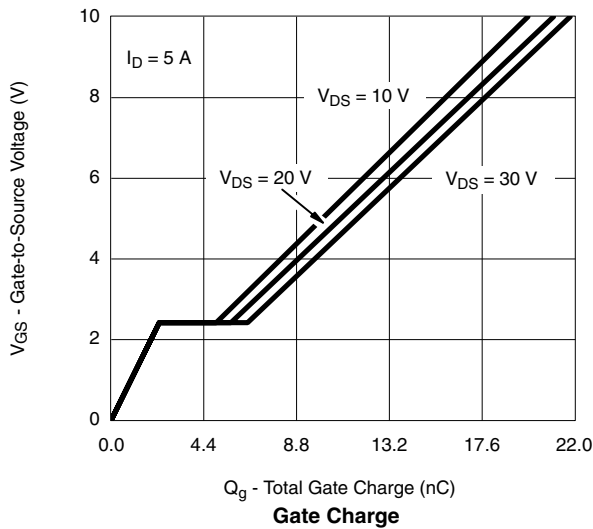
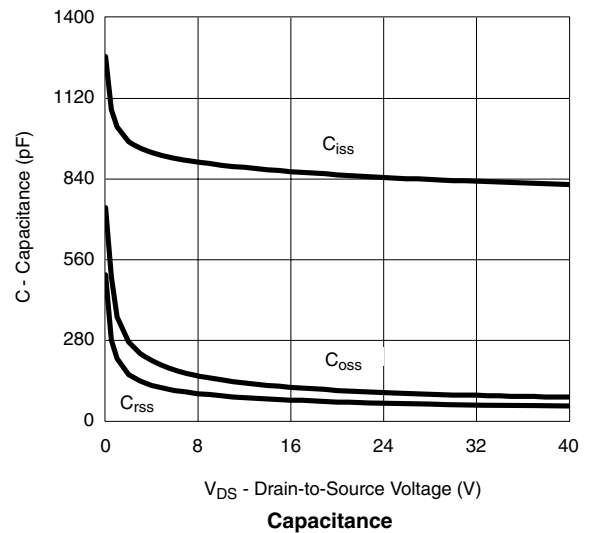
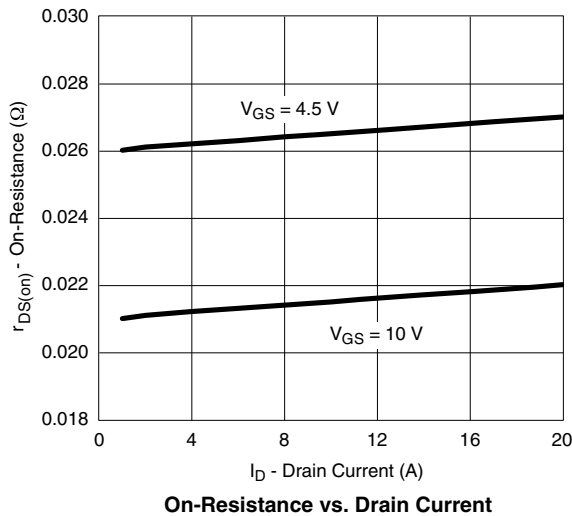
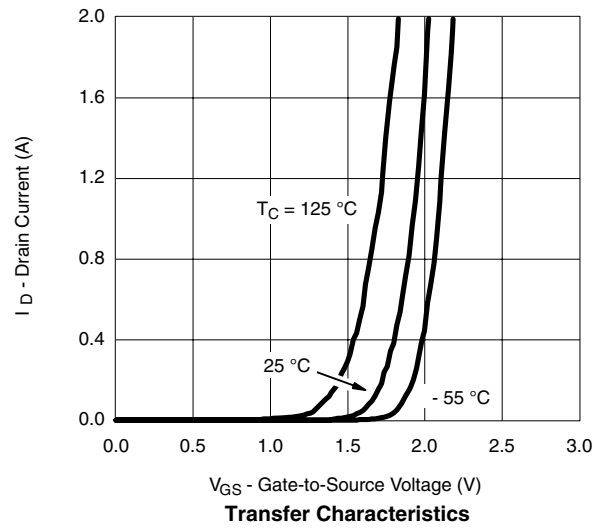
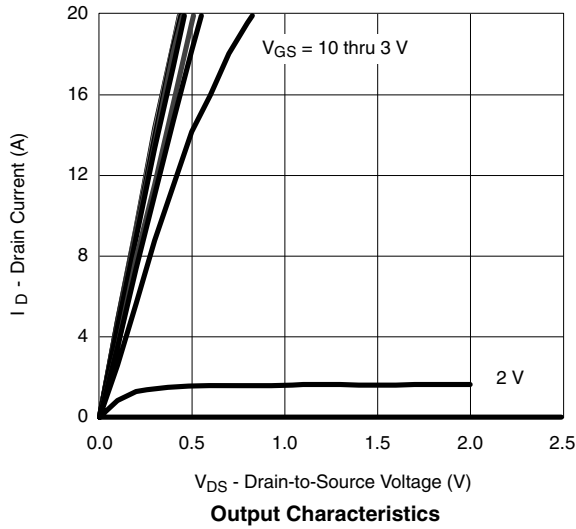
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min	Typ ^a	Max	Unit
Dynamic^a							
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$ P-Channel $V_{DD} = -20\text{ V}, R_L = 4\ \Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\ \Omega$	N-Ch		6	12	ns
			P-Ch		7	14	
Rise Time	t_r		N-Ch		21	32	
			P-Ch		23	35	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		24	36	
			P-Ch		51	77	
Fall Time	t_f		N-Ch		9	15	
			P-Ch		50	80	
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 20\text{ V}, R_L = 4\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$ P-Channel $V_{DD} = -20\text{ V}, R_L = 4\ \Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\ \Omega$	N-Ch		12	20	
			P-Ch		40	60	
Rise Time	t_r		N-Ch		75	115	
			P-Ch		106	160	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		40	60	
			P-Ch		45	70	
Fall Time	t_f		N-Ch		56	85	
			P-Ch		50	75	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	N-Ch			8	A
			P-Ch			-8	
Pulse Diode Forward Current ^a	I_{SM}		N-Ch			35	
			P-Ch			-35	
Body Diode Voltage	V_{SD}	$I_S = 1.5\text{ A}$ $I_S = -1.6\text{ A}$	N-Ch		0.73	1.2	V
			P-Ch		-0.73	-1.2	
Body Diode Reverse Recovery Time	t_{rr}	N-Channel $I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ P-Channel $I_F = -5\text{ A}, di/dt = -100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	N-Ch		26	40	ns
P-Ch			30	45			
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch		21	32	nC
			P-Ch		24	36	
Reverse Recovery Fall Time	t_a		N-Ch		13		ns
			P-Ch		15		
Reverse Recovery Rise Time	t_b	N-Ch		13			
		P-Ch		15			

Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

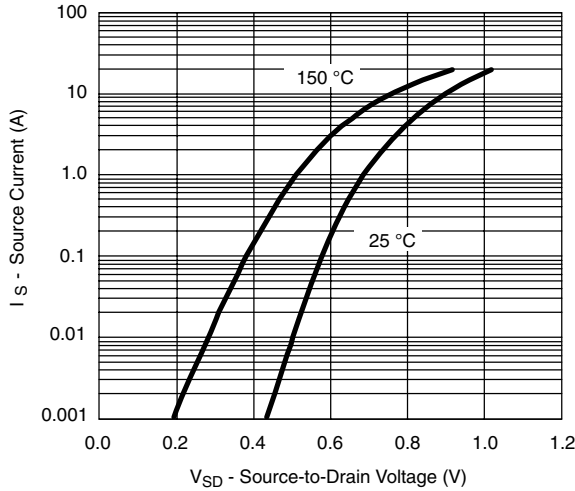
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

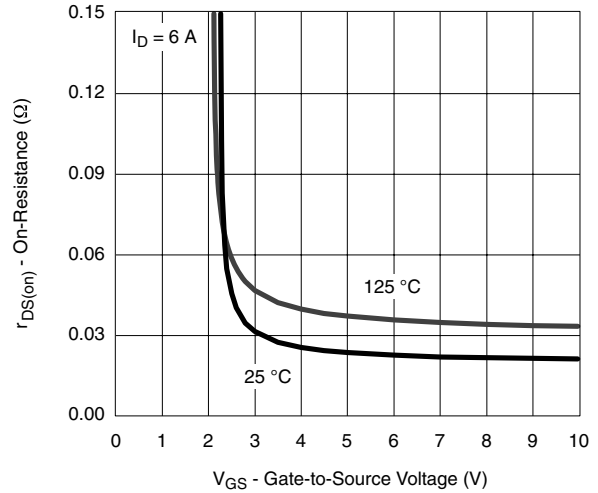




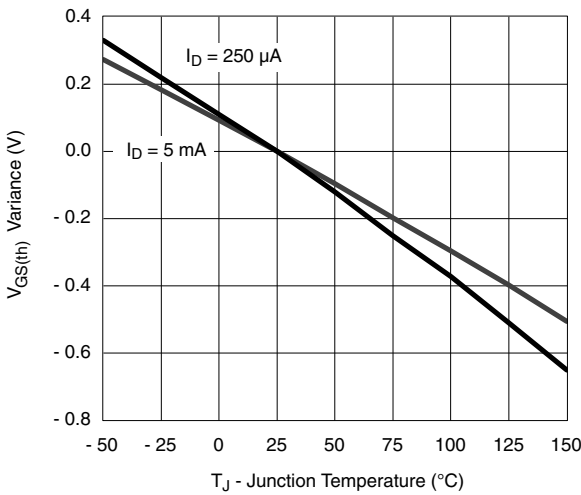
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



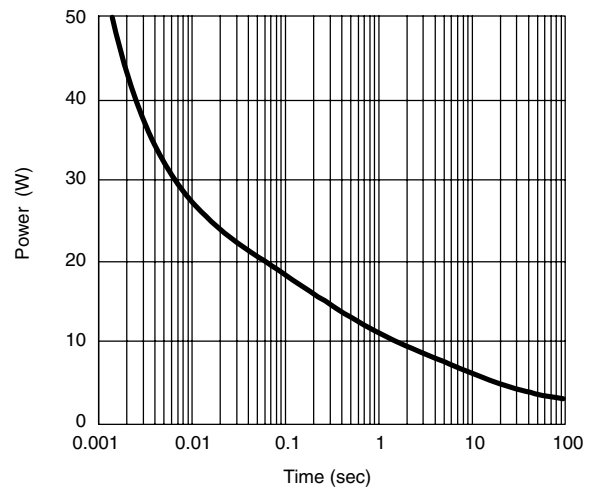
Source-Drain Diode Forward Voltage



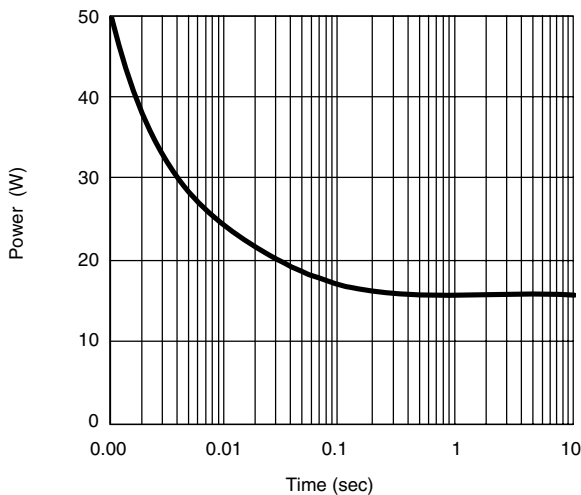
On-Resistance vs. Gate-to-Source Voltage



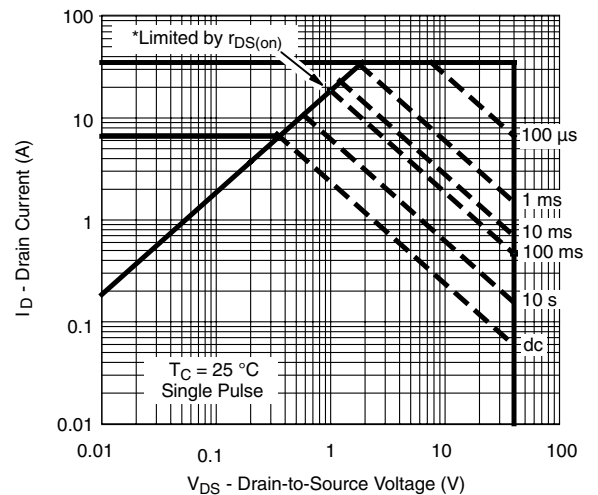
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



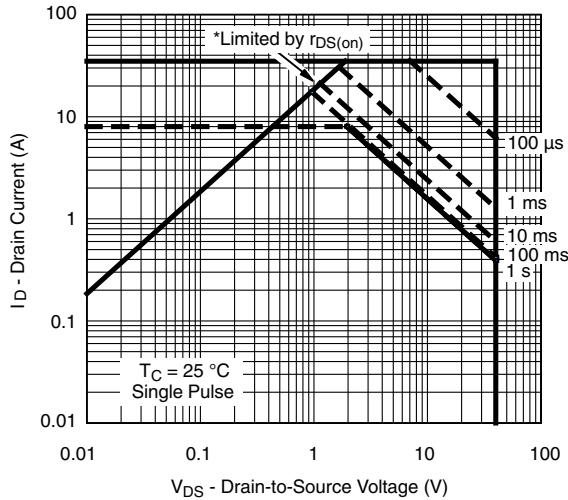
Single Pulse Power, Junction-to-Case



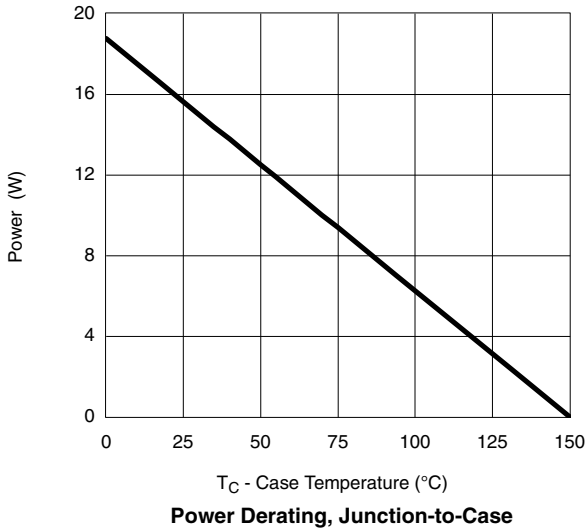
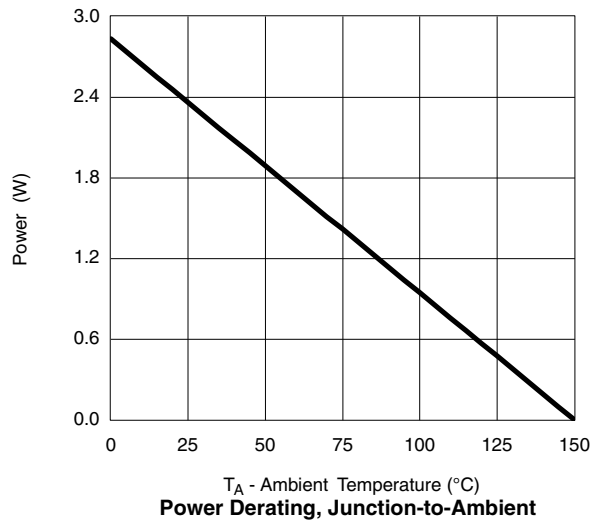
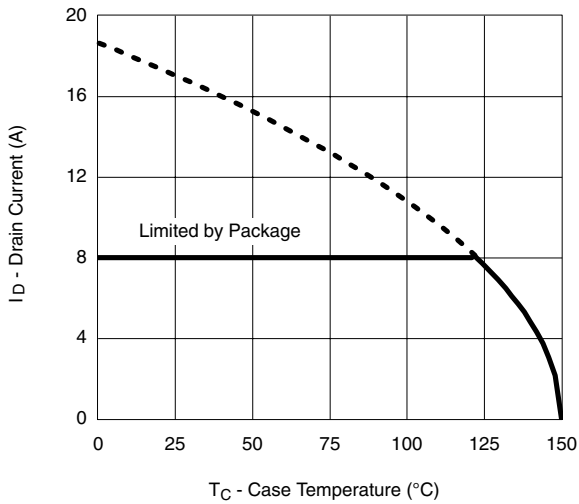
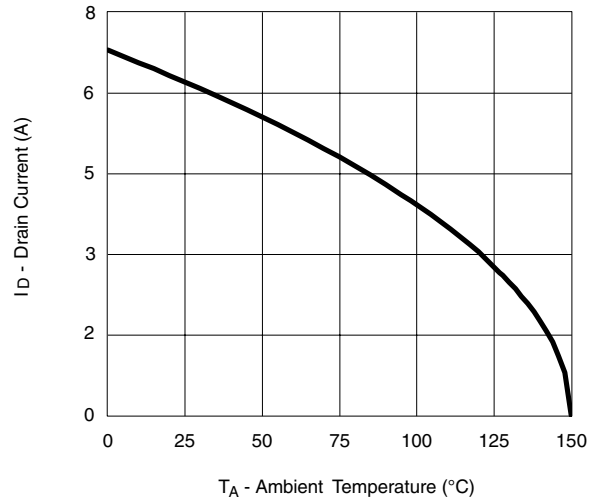
*V_{GS} > minimum V_{GS} at which r_{DS(on)} is specified

Safe Operating Area, Junction-to-Ambient

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted

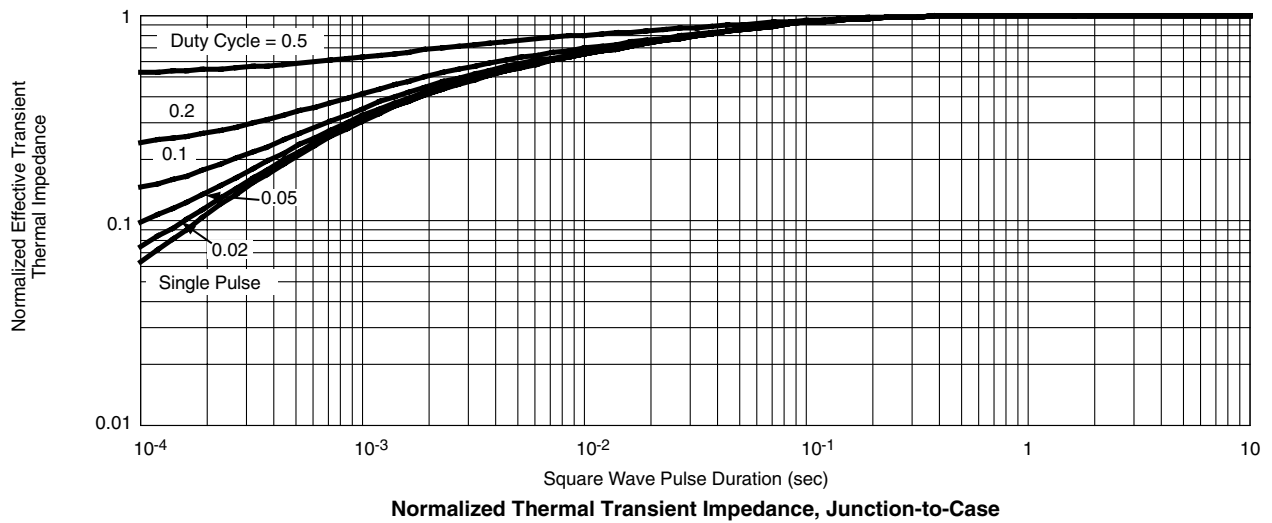
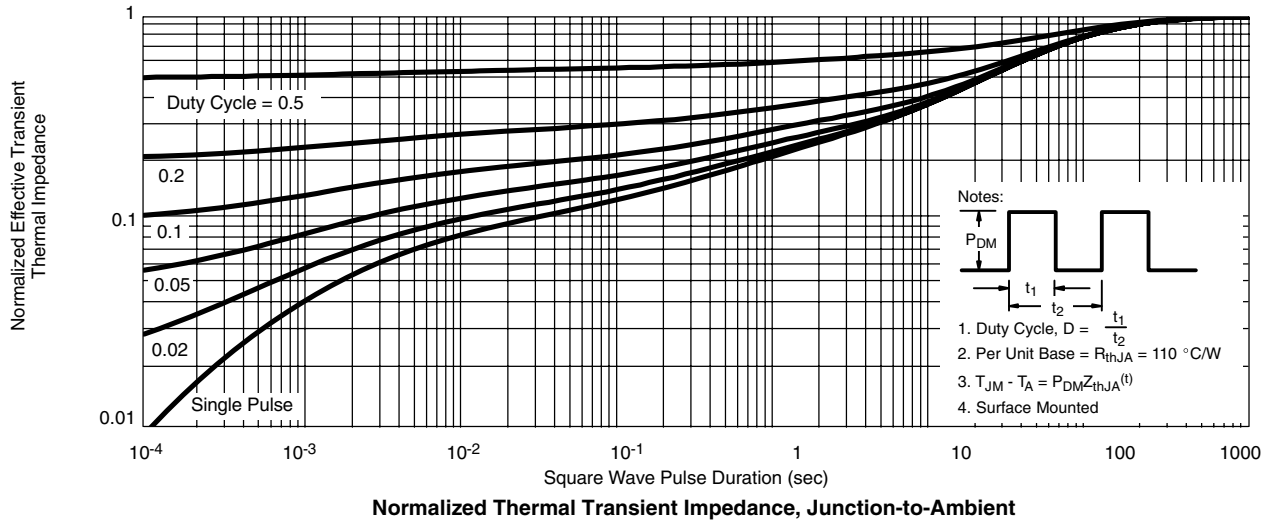


* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

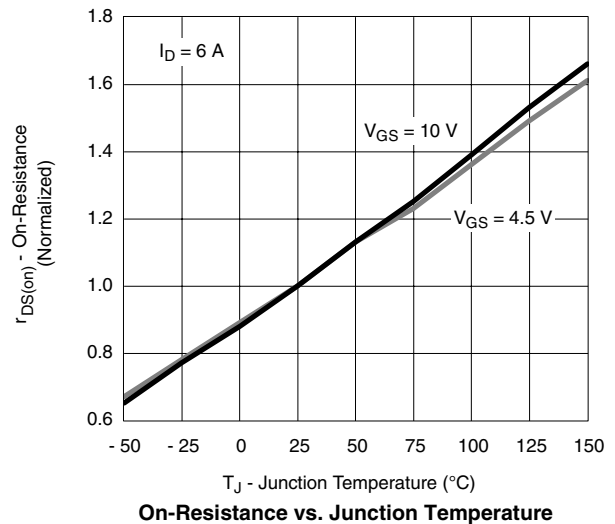
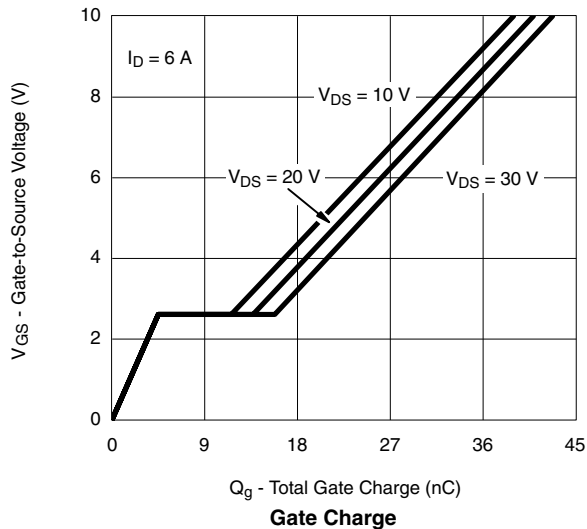
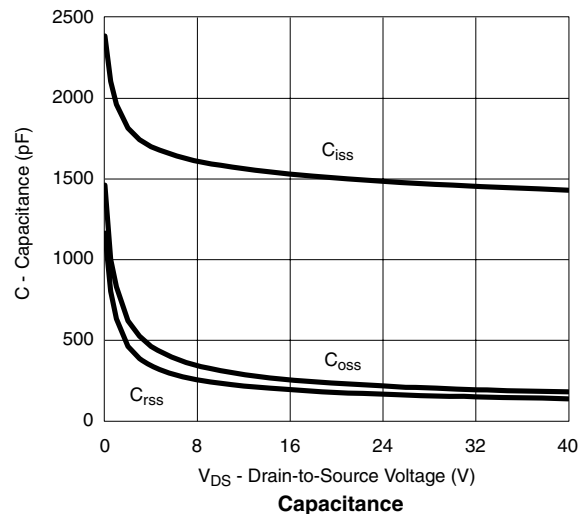
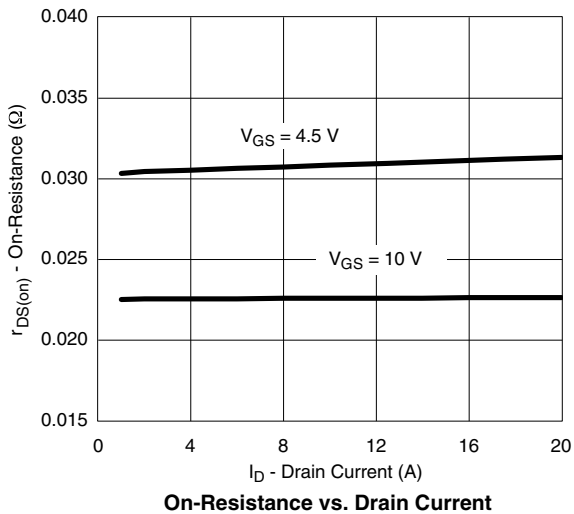
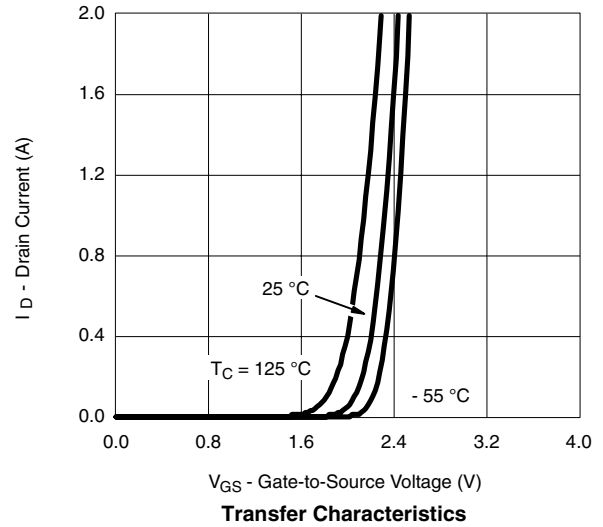
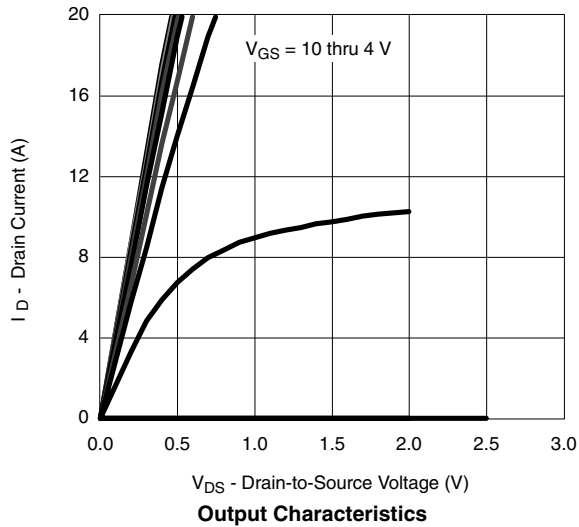


*The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

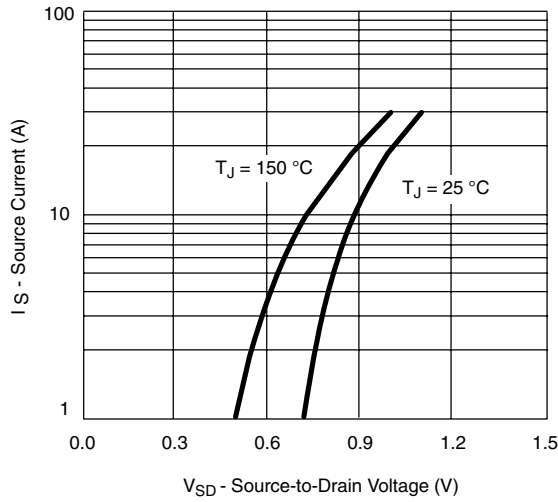
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



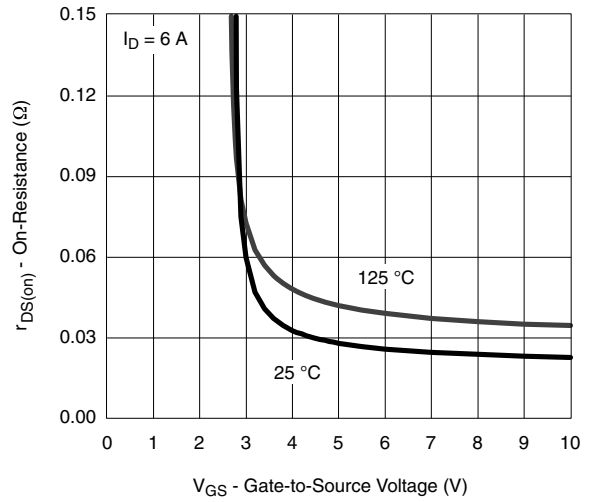
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



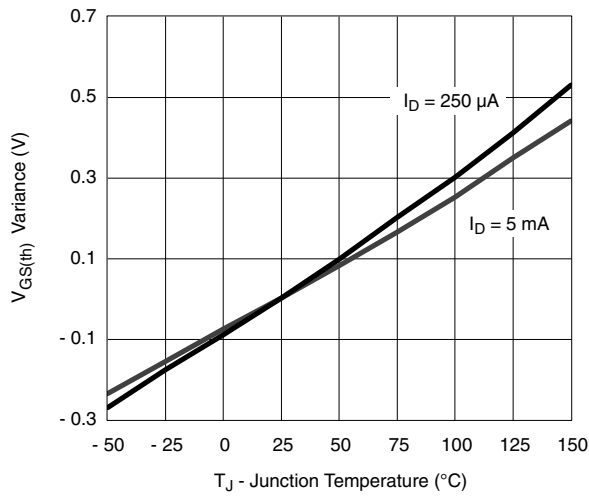
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



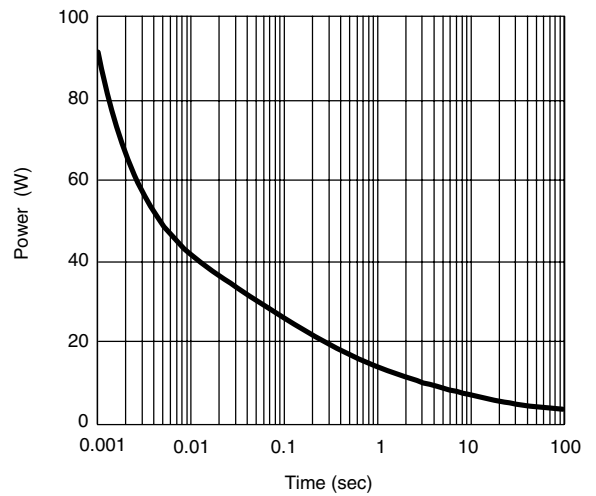
Source-Drain Diode Forward Voltage



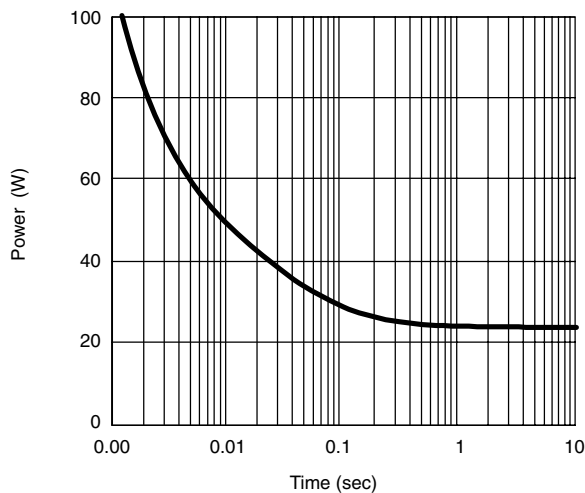
On-Resistance vs. Gate-to-Source Voltage



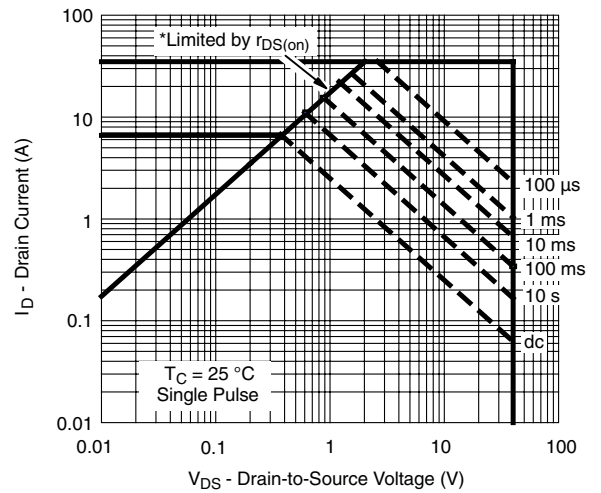
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

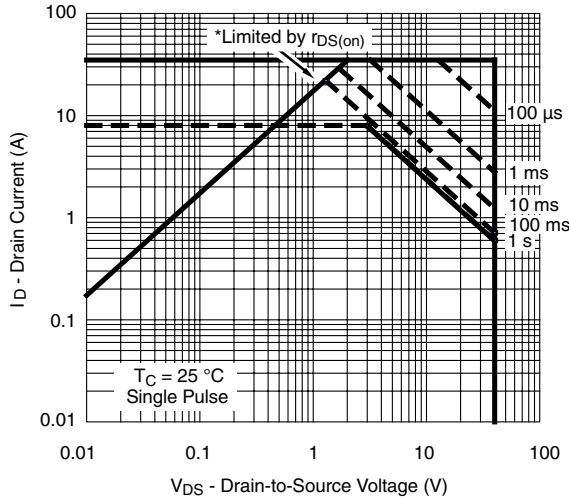


Single Pulse Power, Junction-to-Case

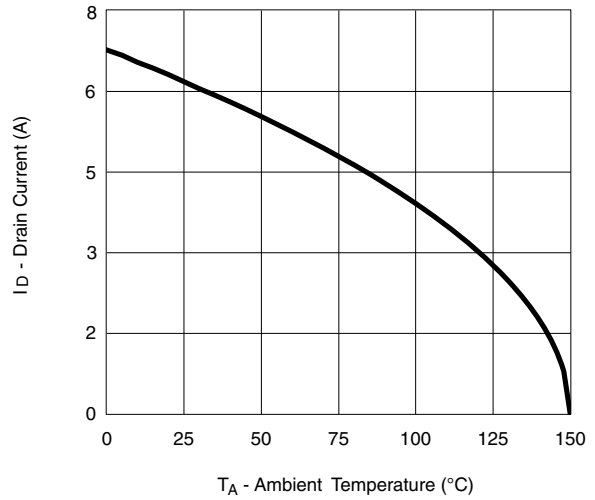


Safe Operating Area, Junction-to-Ambient

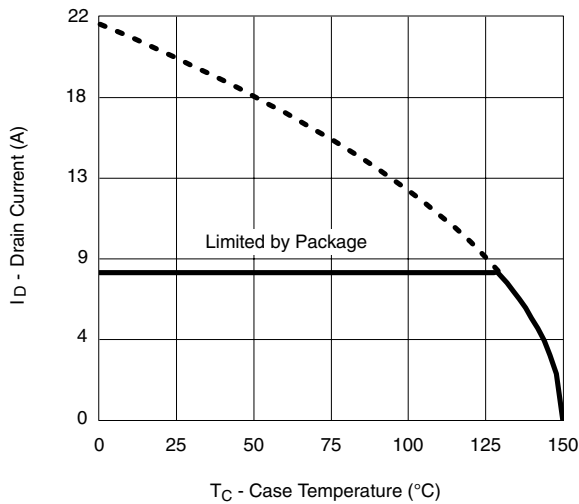
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



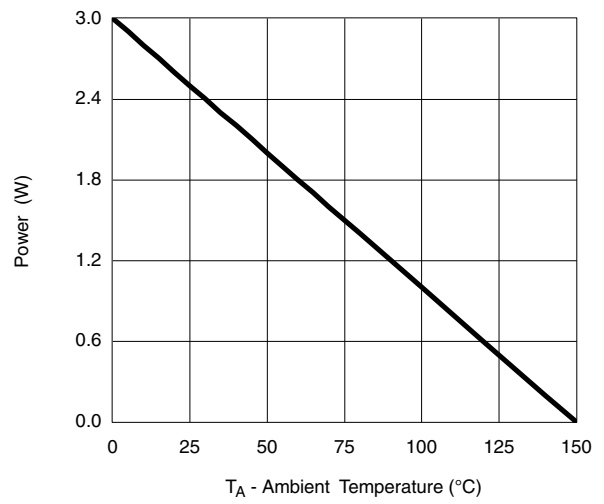
V_{DS} - Drain-to-Source Voltage (V)
 * $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Case



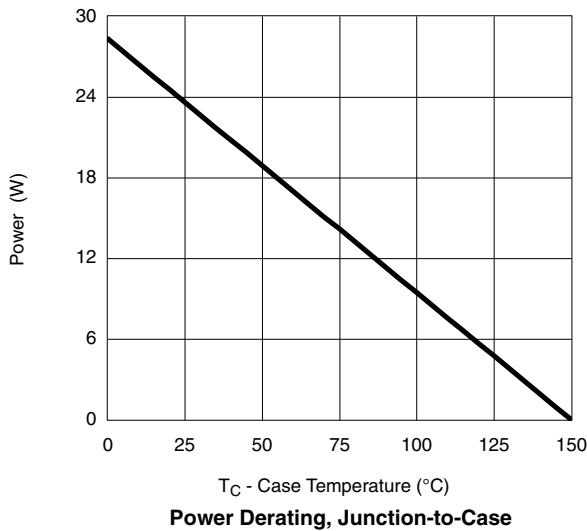
T_A - Ambient Temperature ($^\circ\text{C}$)
Current Derating, Junction-to-Ambient



T_C - Case Temperature ($^\circ\text{C}$)
Current Derating, Junction-to-Case



T_A - Ambient Temperature ($^\circ\text{C}$)
Power Derating, Junction-to-Ambient

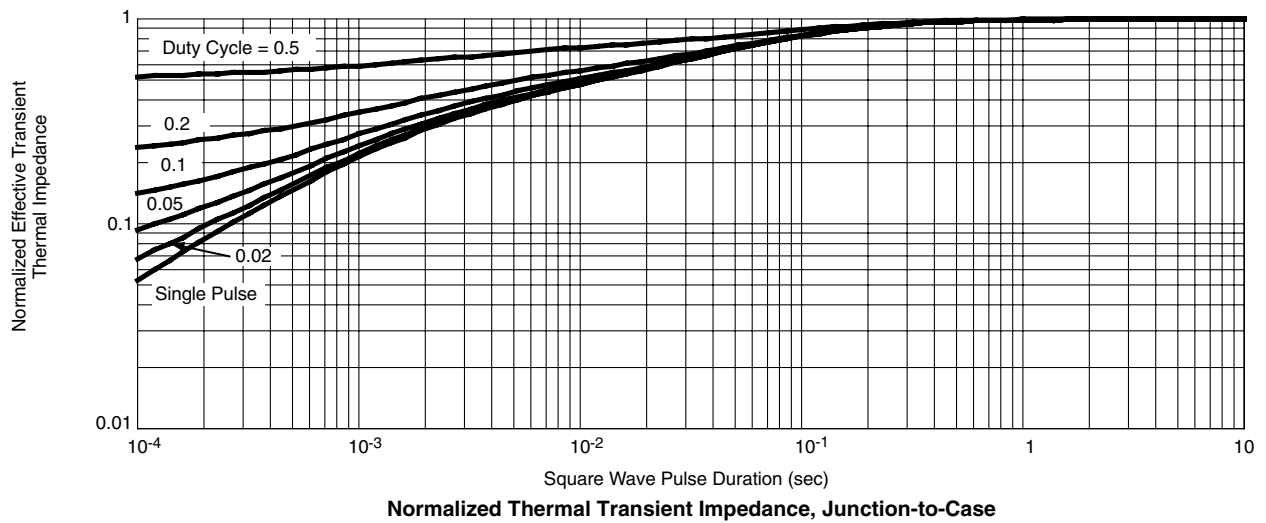
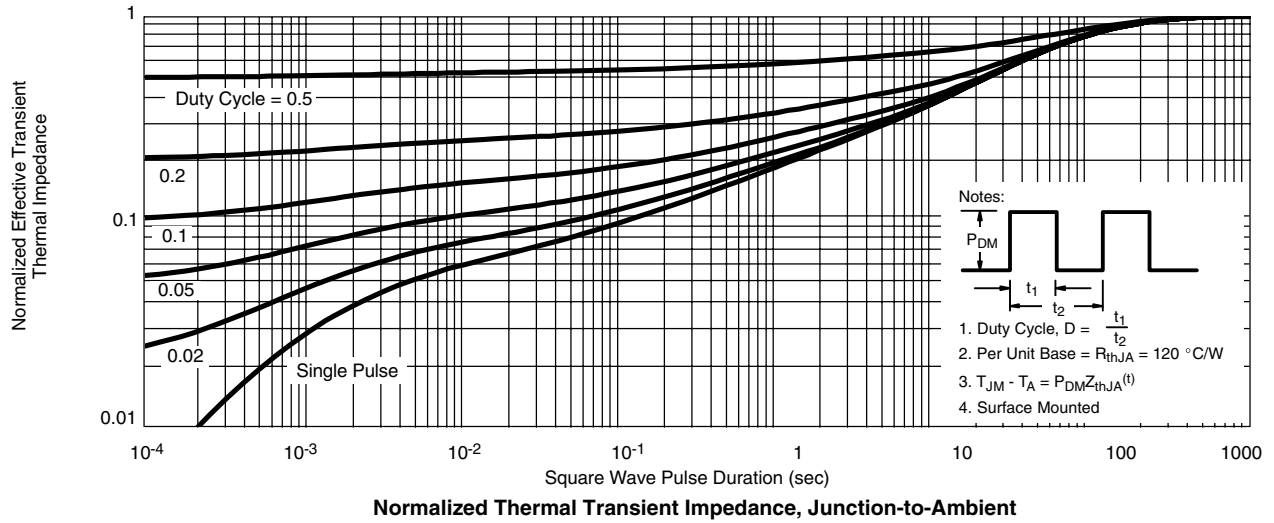


T_C - Case Temperature ($^\circ\text{C}$)
Power Derating, Junction-to-Case

*The power dissipation P_D is based on $T_{J(max)} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless noted



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